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 H01L021/66 ;
 H01L027/10

ABSTRACTED-PUB-NO: DE 10036177A

BASIC-ABSTRACT: NOVELTY - A device for testing semiconductor devices (3) in order to detect faulty devices, has a tunable light source (4) which is capable of projecting light of a given wavelength (λ) and intensity (I) on to the semiconductor device (3) for a given length of time (T), so that with irradiation of the semiconductor device with this light, electrons can cross over from the valence band with a small gap, into the conduction band.

USE - Testing of semiconductor devices by measuring the gap between the valence band and the conduction band, with low values compared with the values obtained with flaw-free semiconductor devices.

ADVANTAGE - Requires no waiting time for temperature changes to take effect and in general long waiting times are avoided. In addition, no cost-intensive changes of equipment are required during testing of different semiconductor devices.

DESCRIPTION OF DRAWING(S) - A schematic representation of the device is given.

Wafer probe 1

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	Document ID	Kind Codes	Source	Issue Date	Pages	
1	JP 2002118156		JPO	20020419	5	APPAP
2	NB890887		IBM TDB	19890801	1	Biast
3	NN87024105		IBM TDB	19870201	2	Non-I
4	DE 10036177 A		DERWENT	20020214	5	Equip

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Patent Application Publication Feb. 21, 2002

US 2002/0021141 A1

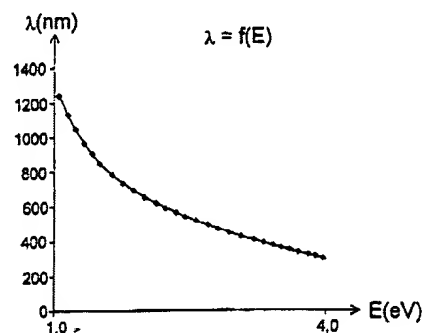


Fig. 1

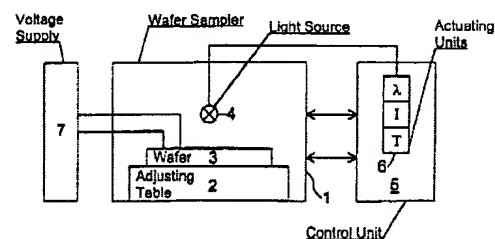


Fig. 2

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(S2) U.S. CL 124/76

(57) ABSTRACT

Publication Classification

(SI) Int. Cl.⁷ G01R 31/26

An apparatus for testing water-level semiconductor devices in particular memory chips in which a tunable light source radiates energy onto the semiconductor devices. The tunable light source is constructed to adjust the radiated light to a specific wavelength and to a specific intensity and to project the light for a predetermined time. When the semiconductor devices are irradiated with the light, electrons in defective ones of the semiconductor devices, in which a distinction between a valence band and a conduction band has a lower value as compared with that of defect-free ones of the semiconductor devices, can be transferred into the conduction band from the valence band. These defective or "poor" semiconductor devices can thus be separated out.

